

# Zhanna V Smagina

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/9889084/publications.pdf>

Version: 2024-02-01

27  
papers

153  
citations

1307594

7  
h-index

1281871

11  
g-index

27  
all docs

27  
docs citations

27  
times ranked

73  
citing authors

#	ARTICLE	IF	CITATIONS
1	Tuning the configuration of quantum dot molecules grown on stacked multilayers of heteroepitaxial islands. <i>Journal of Applied Physics</i> , 2022, 131, 035302.	2.5	2
2	Radiation-Induced Nucleation and Growth of CaSi <sub>2</sub> Crystals, Both Directly during the Epitaxial CaF <sub>2</sub> Growth and after the CaF <sub>2</sub> Film Formation. <i>Nanomaterials</i> , 2022, 12, 1407.	4.1	5
3	Luminescent properties of spatially ordered Ge/Si quantum dots epitaxially grown on a pit-patterned silicon-on-insulator substrate. <i>Journal of Luminescence</i> , 2022, 249, 119033.	3.1	2
4	Groups of Ge nanoislands grown outside pits on pit-patterned Si substrates. <i>Journal of Crystal Growth</i> , 2022, 593, 126763.	1.5	1
5	One-Stage Formation of Two-Dimensional Photonic Crystal and Spatially Ordered Arrays of Self-Assembled Ge(Si) Nanoislands on Pit-Patterned Silicon-On-Insulator Substrate. <i>Nanomaterials</i> , 2021, 11, 909.	4.1	8
6	Laser annealing of epitaxial CaF <sub>2</sub> films on Si. <i>Thin Solid Films</i> , 2021, 735, 138898.	1.8	1
7	Si-based light emitters synthesized with Ge <sup>+</sup> ion bombardment. <i>Journal of Applied Physics</i> , 2021, 130, .	2.5	3
8	Atomic Structure and Optical Properties of CaSi <sub>2</sub> Layers Grown on CaF <sub>2</sub> /Si Substrates. <i>Semiconductors</i> , 2021, 55, 808-811.	0.5	2
9	Luminescence of Spatially Ordered Self-Assembled Solitary Ge(Si) Nanoislands and their Groups Incorporated into Photonic Crystals. <i>Semiconductors</i> , 2020, 54, 853-859.	0.5	6
10	Self-Organization of Ge(Si) Nanoisland Groups on Pit-Patterned Si(100) Substrates. <i>Semiconductors</i> , 2020, 54, 1866-1868.	0.5	1
11	Nucleation of Three-Dimensional Ge Islands on a Patterned Si(100) Surface. <i>Semiconductors</i> , 2018, 52, 1457-1461.	0.5	5
12	Nucleation sites of Ge nanoislands grown on pit-patterned Si substrate prepared by electron-beam lithography. <i>Journal of Applied Physics</i> , 2018, 123, .	2.5	14
13	Study of the Structural and Emission Properties of Ge(Si) Quantum Dots Ordered on the Si(001) Surface. <i>Semiconductors</i> , 2018, 52, 1150-1155.	0.5	7
14	Strain-induced improvement of photoluminescence from the groups of laterally ordered SiGe quantum dots. <i>Applied Physics Letters</i> , 2017, 110, 102101.	3.3	18
15	Unusual narrowing of the ESR line width in ordered structures with linear chains of Ge/Si quantum dots. <i>JETP Letters</i> , 2015, 102, 108-112.	1.4	8
16	Linear chains of Ge/Si quantum dots grown on a prepatterned surface formed by ion irradiation. <i>Semiconductors</i> , 2015, 49, 749-752.	0.5	20
17	Conductance through chains of Ge/Si quantum dots: Crossover from one-dimensional to quasi-one-dimensional hopping. <i>JETP Letters</i> , 2015, 101, 22-26.	1.4	3
18	Chains of quantum dot molecules grown on Si surface pre-patterned by ion-assisted nanoimprint lithography. <i>Applied Physics Letters</i> , 2014, 105, 153106.	3.3	8

#	ARTICLE	IF	CITATIONS
19	Formation of germanium nanoislands on pit-patterned silicon substrates by means of the molecular dynamics method. Optoelectronics, Instrumentation and Data Processing, 2014, 50, 247-251.	0.6	0
20	Three-dimensional model of heteroepitaxial growth of germanium on silicon. Optoelectronics, Instrumentation and Data Processing, 2013, 49, 461-466.	0.6	6
21	Melting of nanocrystals embedded in a crystal matrix heated by nanosecond laser pulses. Journal of Experimental and Theoretical Physics, 2012, 115, 436-444.	0.9	2
22	Nucleation of Ge nanoislands on Si by pulsed ion irradiation. , 2010, , .		0
23	Application of XAFS spectroscopy to studying the microstructure and electronic structure of quantum dots. Journal of Surface Investigation, 2007, 1, 26-34.	0.5	4
24	Elemental composition of nanoclusters formed by pulsed irradiation with low-energy ions during Ge/Si epitaxy. JETP Letters, 2004, 79, 333-336.	1.4	4
25	Self-organization of an ensemble of Ge nanoclusters upon pulsed irradiation with low-energy ions during heteroepitaxy on Si. JETP Letters, 2001, 74, 267-269.	1.4	16
26	Effects of low-energy ion beam action on Ge/Si heteroepitaxy from molecular beam. JETP Letters, 2000, 72, 131-133.	1.4	7
27	Dependence of the Luminescence Properties of Ordered Groups of Ge(Si) Nanoislands on the Parameters of the Pit-Patterned Surface of a Silicon-on-Insulator Substrate. Semiconductors, 0, , .	0.5	0